IN THE CLAIMS:

1. (cancelled)

2. (currently amended) A manufacturing method of a bonded substrate having ~~its~~ a final active layer thickness of 200nm or ~~lower~~ less, ~~by performing an~~ comprising etching ~~process on~~ a surface of an active layer on a support substrate, said active layer being a layer formed over ~~a~~ the support substrate by cleaving off a portion of an active layer wafer, ~~for the purpose of controlling~~ to control the thickness of said active layer, said etching ~~process~~ being carried out ~~by~~ using a solution having an etching effect so as to ~~achieve the etching by~~ etch in a range of 1nm to 1μm, said solution being a solution having pH 9 or higher and containing alkaline chemicals and an oxidizer.

3. (currently amended) A manufacturing method of a bonded substrate in accordance with claim 2, in which an etching rate in said etching ~~process~~ is not greater than 100nm/min.

4 - 7. (cancelled)

8. (currently amended) A manufacturing method of a bonded substrate in accordance with claim 2, in which after said etching ~~process~~, a thickness of said active layer is measured and based on said obtained measurement data, said etching ~~process~~ is repeated until said thickness of the active layer across its entire area comes near to a predetermined ~~value of~~ thickness of the final active layer.

9. (currently amended) A manufacturing method of a bonded substrate in accordance with claim 3, in which after said etching ~~process~~, a thickness of said active layer is measured and based on said obtained measurement data, said etching ~~process~~ is repeated until said thickness of the active layer across its entire area comes near to a predetermined ~~value of~~ thickness of the final active layer.

10 - 13. (cancelled)

14. (currently amended) A manufacturing method of a bonded substrate in accordance with claim 2, in which one of following steps is performed on said active layer surface of said bonded substrate before said etching ~~process~~, said steps including:

(1) a step of chemical mechanical polishing ~~process~~ taking advantage of a chemical effect and a mechanical effect at the same time;

(2) a step of hydrogen treating ~~process~~ for performing a heat treatment in a reducing atmosphere containing hydrogen; and

(3) a step of forming a silicon oxide film over said active layer and then removing said silicon oxide film along with a damaged portion of said active layer, which has been created in said cleaving ~~process~~.

15. (currently amended) A manufacturing method of a bonded substrate in accordance with ~~claim 2~~ claim 3, in which one of following steps is performed on said active layer surface of said bonded substrate before said etching ~~process~~, said steps including:

(1) a step of chemical mechanical polishing ~~process~~ taking advantage of a chemical effect and a mechanical effect at the same time;

(2) a step of hydrogen treating ~~process~~ for performing a heat treatment in a reducing atmosphere containing hydrogen; and

(3) a step of forming a silicon oxide film over said active layer and then removing said silicon oxide film along with a

damaged portion of said active layer, which has been created in said cleaving ~~process~~.

16. (cancelled)